N-Channel 150V Switch MOSFET

Features

- Typ R_{DS}(on)=0.8Ω @ V_{GS} =4.5V,I_D=2A
- · Fast Switching Speed
- · Low Gate Charge
- High Power and Current Handling Capability
- ESD Rating:2000V HBM

General Description

This N-Channel MOSFET is produced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet

Applications

- DC Switch
- Led Driver



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Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units		
V _{DSS}	Drain to Source V	Drain to Source Voltage			150	V	
V _{GSS}	Gate to Source Vo	Gate to Source Voltage			±10	V	
	Drain Curren - Continuous (Silicon Limited) T _C = 25°C			2.0			
	- Continuous(Package Limited) T _C = 25°C			3	A		
D	- Continuous			T _C = 25°C(Note 1a)	4		
	- Pulsed			6	Α		
E _{AS}	Single Pulsed Avalanche Energy			(Note 3)	1.0	mJ	
P _D	Power Dissipation	- T _C = 25°C	(Note 1a)	1.25	W		
		- T _A = 25°C	(Note 1b)	0.2	W/°C		
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +155	°C		

Thermal Characteristics

Symbol	Parameter	Ratings	Units		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	5.0	0C/M	
R _{0JA}	Thermal Resistance, Junction to Ambient	(Note 1a)	100	C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
MT3455	MT3455	SOT-23	-	-	3000

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	150			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu A$, Referenced to 25°C		0.09		V/°C
IDSS	7 0 1 1/1 5 2 0 1	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
	Zero Gate Voltage Drain Current	V _{DS} = 80 V, T _C = 125°C			10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Cha	ractoristics	·				
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA		1.1		V
R _{DS(on)}	Static Drain-Source V _{GS} =4.5 V, I _D = 1 A			0.8		Ω
9 _{FS}	Forward Transconductance	V _{DS} = 30 V, I _D = 1 A (Note 4)		11		S
Dynam C _{iss}	ic Characteristics	$V_{} = 25 V V_{} = 0 V$			1500	pF
Coss	Output Capacitance	Capacitance $f = 1.0 \text{ MHz}$			200	pF
C _{rss}	Reverse Transfer Capacitance				160	pF
Switchi	ng Characteristics					1
t _{d(on)}	Turn-On Delay Time	$y_{1} = 50y_{1} + 500$		6		ns
t _r	Turn-On Rise Time	$V_{DD} = 50 V, I_D = 19 A,$		12		ns
t _{d(off)}	Turn-Off Delay Time	- rg - 23 22		4.5		ns
t _f	Turn-Off Fall Time	(Note 4, 5)		16		ns
Q _q	Total Gate Charge	Vps = 80 V. lp = 19 A.		15		nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		8		nC
Q _{gd}	Gate-Drain Charge	(Note 4, 5)		5		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
l _s	Maximum Continuous Drain-Source Diode Forward Current				6	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				6	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 15.6 A			1.2	V
trr	Reverse Recovery Time	$V_{CS} = 0 V. I_{S} = 19 A.$		80		ns

Qrr

 $\begin{array}{l} \textbf{Notes:} \\ 1. \mbox{ Repetitive Rating : Pulse width limited by maximum junction temperature} \\ 2. \mbox{ L} = 1.35mH, I_{AS} = 15.6A, V_{DD} = 25V, R_G = 25 \ \Omega, \mbox{ Starting } T_J = 25^\circ C \\ 3. \mbox{ I}_{SD} \leq 19A, \ d'dt \leq 300 \ \mu s, V_{DD} \leq BV_{DSS}, \mbox{ Starting } T_J = 25^\circ C \\ 4. \ Pulse Test : Pulse width \leq 300 \ \mu s, \ Duty \ cycle \leq 2\% \\ 5. \ Essentially independent of operating temperature \end{array}$

Reverse Recovery Charge

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0.195

(Note 4)

μC

 dI_F / dt = 100 A/µs



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FIGURE 10. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms



FIGURE 11. SWITCHING TIME TEST CIRCUIT



FIGURE 13. GATE CHARGE TEST CIRCUIT



FIGURE 12. RESISTIVE SWITCHING WAVEFORMS



FIGURE 14. GATE CHARGE WAVEFORMS





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